

**P-Channel 30-V (D-S) MOSFET**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

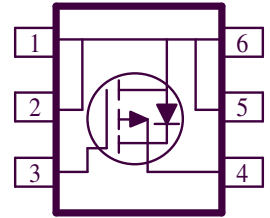
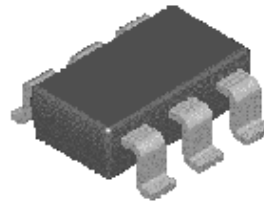
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-30.0	0.056 @ $V_{GS} = -10V$	-4.0
	0.083 @ $V_{GS} = -4.5V$	-3.4



RoHS  
COMPLIANT  
HALOGEN  
FREE



Protected



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ C$	-4.0	A
	$T_A = 70^\circ C$	-3.2	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	$\pm 20$	
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	-1.7	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ C$	2.0	W
	$T_A = 70^\circ C$	1.3	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 5$ sec	62.5	$^\circ C/W$
	Steady state	110	$^\circ C/W$

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

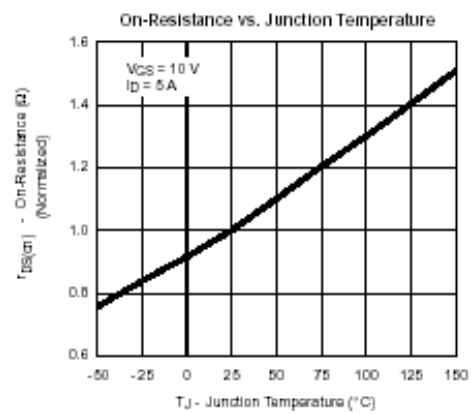
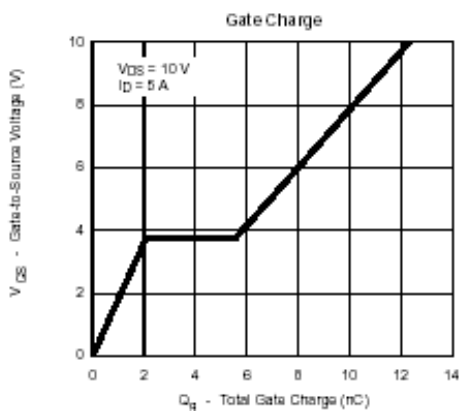
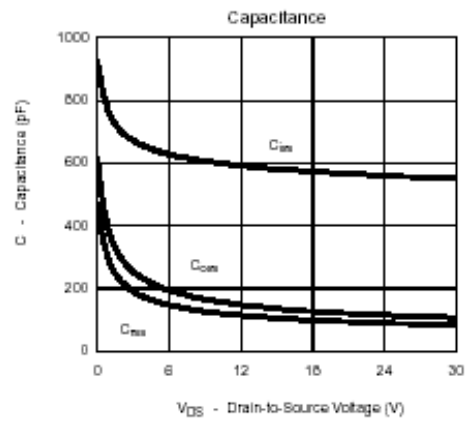
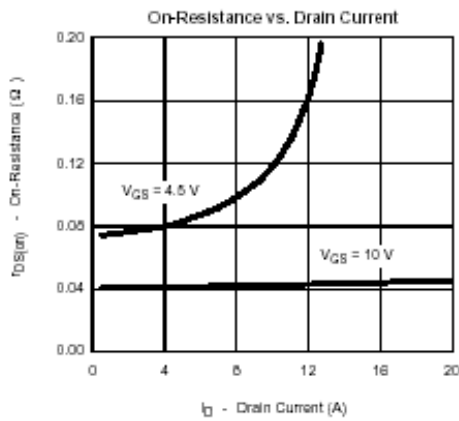
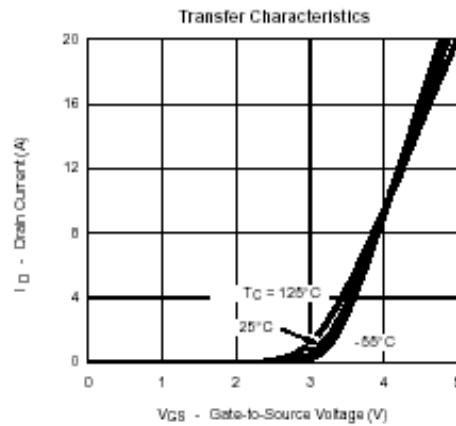
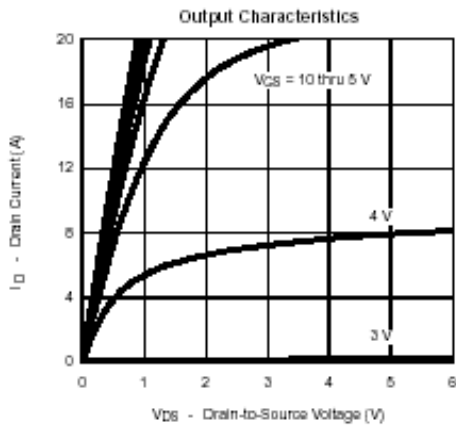
SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
<b>Static</b>						
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 uA	-1			
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -16 V, V <sub>GS</sub> = 0 V			-1	uA
		V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			-5	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = -5 V, V <sub>GS</sub> = -4.5 V	-20			A
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -4.0 A			56	mΩ
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.4 A			83	
Forward Transconductance <sup>A</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -3.4 A		10		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.3 A, V <sub>GS</sub> = 0 V		-0.8		V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = -5 V, I <sub>D</sub> = -4.0 A		6.4		nC
Gate-Source Charge	Q <sub>gs</sub>			2.0		
Gate-Drain Charge	Q <sub>gd</sub>			3.8		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -20 V, R <sub>L</sub> = 6 Ω, I <sub>D</sub> = -1 A, V <sub>GEN</sub> = -10 V		7		ns
Rise Time	t <sub>r</sub>			10		
Turn-Off Delay Time	t <sub>d(off)</sub>			30		
Fall-Time	t <sub>f</sub>			22		

## Notes

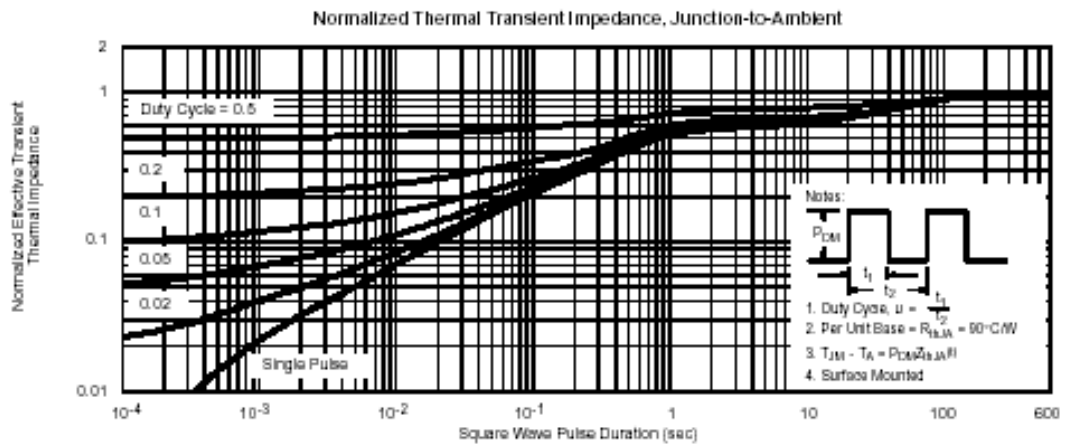
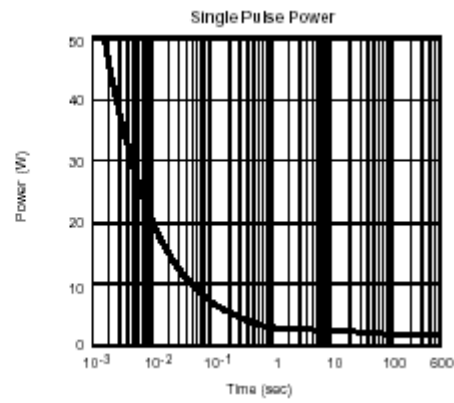
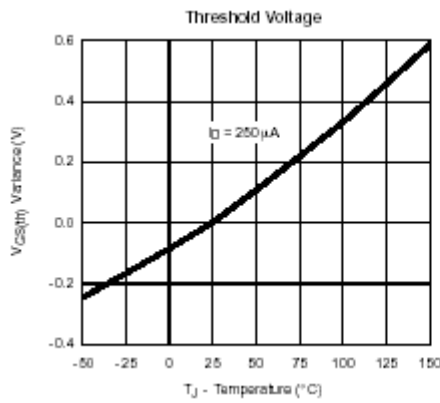
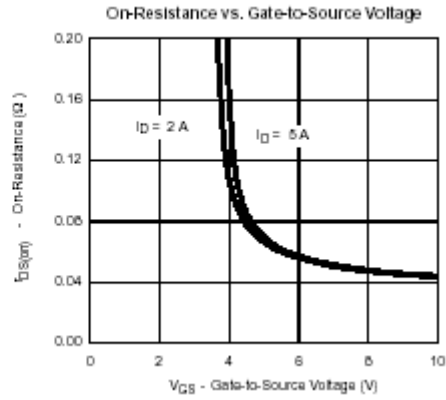
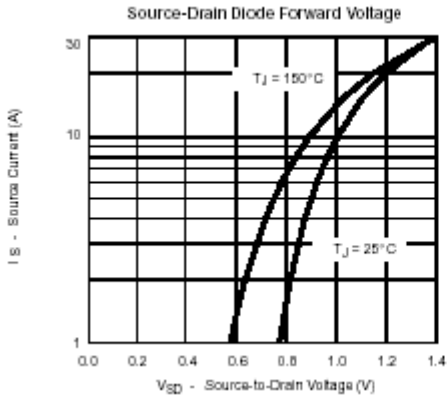
- Pulse test: PW ≤ 300us duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

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### Typical Electrical Characteristics (P-Channel)

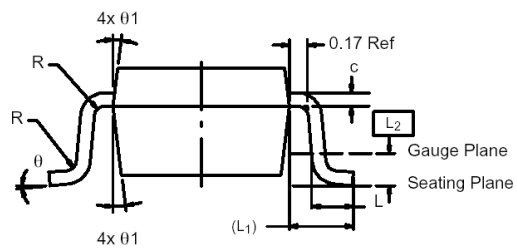
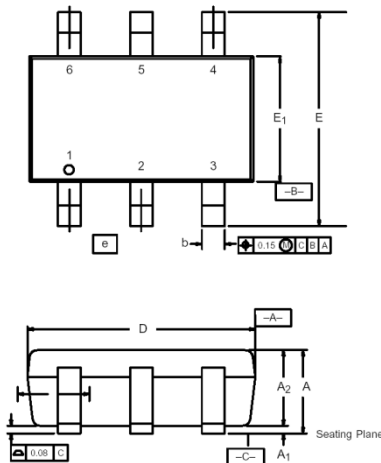


### Typical Electrical Characteristics (P-Channel)



Package Information

TSOP-6: 6LEAD



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	–	1.10	0.036	–	0.043
A <sub>1</sub>	0.01	–	0.10	0.0004	–	0.004
A <sub>2</sub>	0.84	–	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
L	0.35	–	0.50	0.014	–	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	–	–	0.004	–	–
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		